**Product data sheet** 

## 1. General description

Planar passivated four quadrant triac in a SOT78 (T0-220AB) plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance.

### 2. Features and benefits

- High blocking voltage capability
- High noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants

## 3. Applications

- General purpose motor controls
- General purpose switching

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	N	/lin	Тур	Max	Unit
$V_{DRM}$	repetitive peak off- state voltage		-		-	600	V
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 ^{\circ}C$ ; $t_p = 20 \text{ms}$ ; Fig. 4; Fig. 5	-	-	-	190	A
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 91 °C; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-		-	25	A
Static charac	cteristics						,
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	6	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	-	10	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	11	35	mA





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G+;	-	23	70	mA
		T <sub>j</sub> = 25 °C; <u>Fig. 7</u>				

# 5. Pinning information

Table 2. Pinning information

2 T2 I	main terminal 1 main terminal 2 gate	mb	T2—T1 G sym051
3 G (	gate		sym051
- ,	-		ŕ
mb T2 r			
	mounting base; main terminal 2	1 2 3 TO-220AB (SOT78)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BTA140-600	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

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# 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 91 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	25	Α
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; $Fig. 4$ ; $Fig. 5$	-	190	Α
		full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 16.7 ms	-	209	Α
l <sup>2</sup> t	I2t for fusing	t <sub>p</sub> = 10 ms; SIN	-	180	A <sup>2</sup> s
dl <sub>T</sub> /dt	rate of rise of on-state current	$I_T$ = 30 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/ $\mu$ s; T2+ G+	-	50	A/µs
		$I_T$ = 30 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/ $\mu$ s; T2+ G-	-	50	A/µs
		$I_T$ = 30 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/ $\mu$ s; T2- G-	-	50	A/µs
		$I_T$ = 30 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/ $\mu$ s; T2- G+	-	10	A/µs
I <sub>GM</sub>	peak gate current		-	2	Α
P <sub>GM</sub>	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

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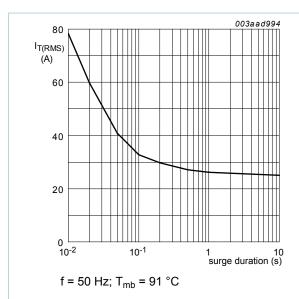


Fig. 1. RMS on-state current as a function of surge duration; maximum values

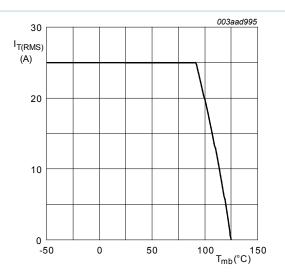
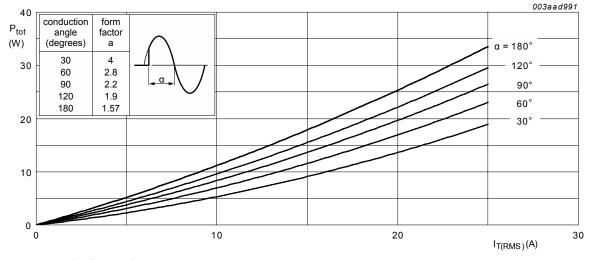


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values



 $\alpha$  = conduction angle

 $a = form factor = I_{T(RMS)} / I_{T(AV)}$ 

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

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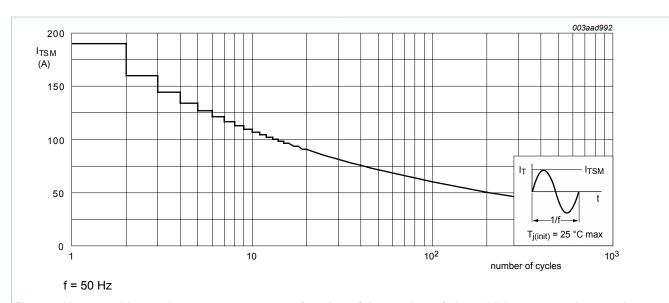
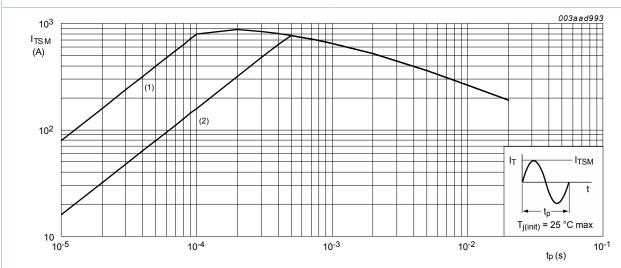


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



t<sub>p</sub> ≤ 20 ms

(1) dI<sub>T</sub>/dt limit

(2) T2- G+ quadrant limit

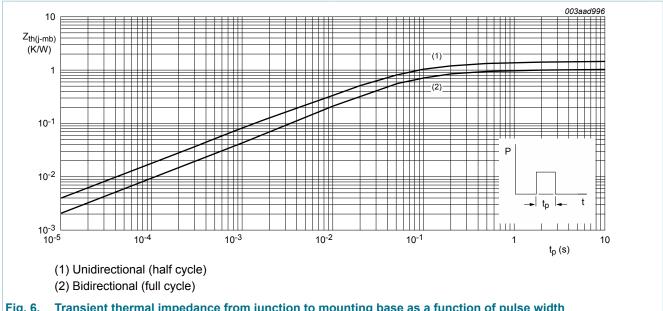
Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

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### **Thermal characteristics**

Table 5. **Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance	full cycle; Fig. 6	-	-	1	K/W
	from junction to mounting base	half cycle; Fig. 6	-	-	1.4	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	60	-	K/W



Transient thermal impedance from junction to mounting base as a function of pulse width

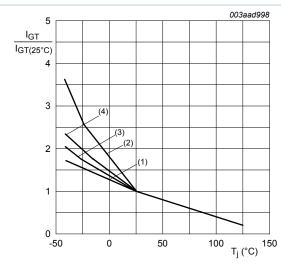
**4Q Triac** 

## 9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	6	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{ G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	10	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	-	11	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G+;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 7}}{}$	-	23	70	mA
L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	8	40	mA
	$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 8$	-	30	60	mA	
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 8$	-	18	40	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; T2- G+;}$ $T_j = 25 \text{ °C; } Fig. 8$	-	15	60	mA
l <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; T2+; <u>Fig. 9</u>	-	7	60	mA
		V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; T2-; <u>Fig. 9</u>	-	12	60	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.3	1.55	V
V <sub>GT</sub>	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.25	0.4	-	V
l <sub>D</sub>	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic ch	naracteristics		· · · · · · · · · · · · · · · · · · ·	-	1	-
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	100	300	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D$ = 400 V; $T_j$ = 95 °C; $dI_{com}/dt$ = 9 A/ ms; $I_T$ = 25 A; gate open circuit	-	10	-	V/µs
gt	gate-controlled turn-on time	$I_{TM}$ = 30 A; $V_D$ = 600 V; $I_G$ = 0.1 A; $dI_G/$ dt = 5 A/µs	-	2	-	μs

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- (1) T2+ G+
- (2) T2+ G-
- (3) T2- G-
- (4) T2- G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

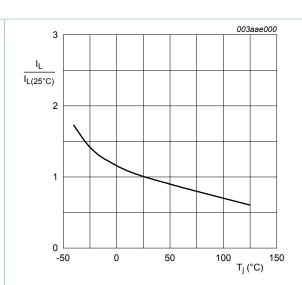


Fig. 8. Normalized latching current as a function of junction temperature

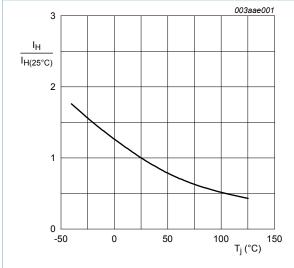
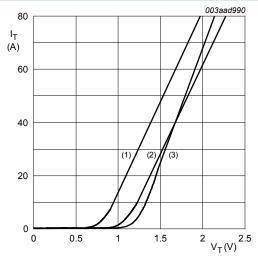


Fig. 9. Normalized holding current as a function of junction temperature



 $V_0 = 1.073 \text{ V}; R_s = 0.015 \Omega$ 

(1) T<sub>i</sub> = 125 °C; typical values

(2) T<sub>i</sub> = 125 °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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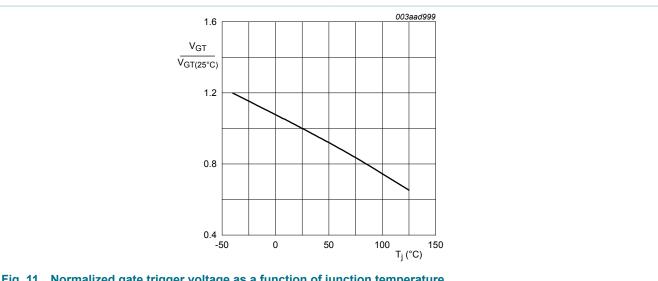
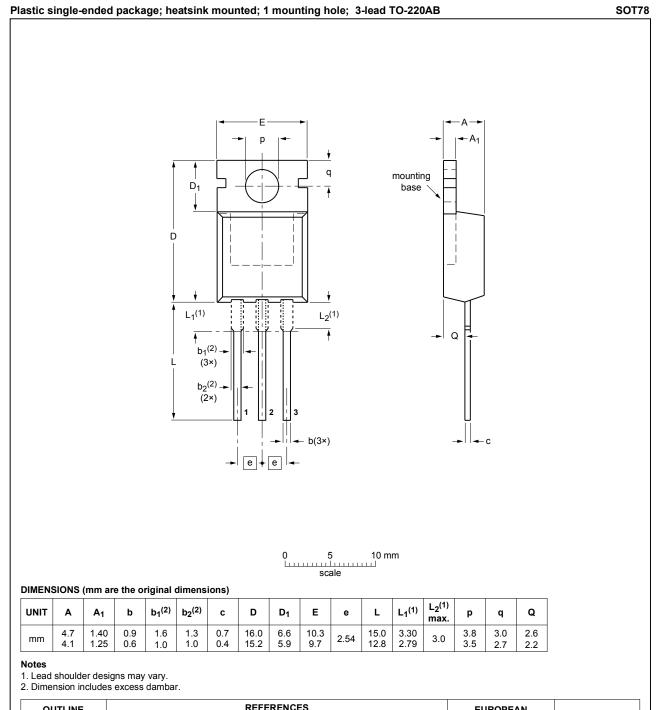


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

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## 10. Package outline



OUTLINE	LINE REFERENCES		EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	1330E DATE
SOT78		3-lead TO-220AB	SC-46		<del>08-04-23</del> 08-06-13

Fig. 12. Package outline TO-220AB (SOT78)

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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